



ACTIVE DEVICES

Butterfly packaged high-speed and low leakage InGaAs quantum well photodiode for 2000nm wavelength systems

H. Yang, N. Ye, R. Phelan, J. O'Carroll, B. Kelly, W. Han, X. Wang, N. Nudds, N. MacSuibhne, F. Gunning, P. O'Brien, F.H. Peters and B. Corbett

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High speed AlInGaAs quantum well waveguide photodiode for wavelengths around 2 microns

Hua Yang, Nan Ye, Agnieszka Gocalinska, Marina Manganaro, Kevin Thomas, Emanuele Pelucchi, Brendan Roycroft, Frank Peters and Brian Corbett

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A high speed waveguide photodiode fabricated with AlInGaAs/AlInGaAs multiple quantum well system for around 2 micron wavelength optical detection is reported. The photodiode shows efficient optical absorption around 2 μm wavelength and dark current as low as 15nA under -3V as well as 10Gb/s high speed operation.

In_{0.75}Ga_{0.25}As/InP Multiple Quantum Well Discrete Mode Laser Diode Emitting at 2 μm

R. Phelan, J. O'Carroll, D. Byrne, C. Herbert, J. Somers, B. Kelly

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A discrete mode laser diode fabricated in the InGaAs/InP multiple quantum well system and emitting single mode at $\lambda=2 \mu\text{m}$ is reported. The laser had an ex-facet output power > 5mW at 25oC and the laser operated mode hop free in the temperature range -5 to 55oC.

<http://ieeexplore.ieee.org/xpl/articleDetails.jsp?arnumber=6138292>